2SD1138

Silicon NPN Triple Diffused

HITACHI

Application

Low frequency high voltage power amplifier TV vertical deflection output complementary pair with 2SB861

Outline

TO-220AB

1. Base
2. Collector (Flange)
3. Emitter

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	200	V
Collector to emitter voltage	V_{CEO}	150	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I_C	2	A
Collector peak current	$I_{C\ (peak)}$	5	A
Collector power dissipation	P_C	1.8	W
	P_C*[1]	30	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–45 to +150	°C

Note: 1. Value at T_C = 25°C.

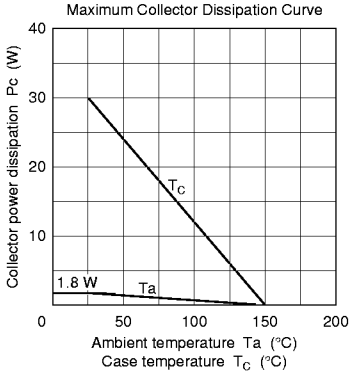
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	150	—	—	V	I_C = 50 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	—	—	V	I_E = 5 mA, I_C = 0
Collector cutoff current	I_{CEO}	—	—	1	µA	V_{CB} = 120 V, I_E = 0
DC current transfer ratio	h_{FE1}*[1]	60	—	320		V_{CE} = 4 V, I_C = 50 mA
	h_{FE2}	60	—	—		V_{CE} = 10 V, I_C = 500 mA*[2]
Collector to emitter saturation voltage	$V_{CE\ (sat)}$	—	—	3.0	V	I_C = 500 mA, I_B = 50 mA*[2]
Base to emitter voltage	V_{BE}	—	—	1.0	V	V_{CB} = 4 V, I_C = 50 mA
Collector output capacitance	Cob	—	20	—	pF	V_{CB} = 100 V, I_E = 0, f = 1 MHz

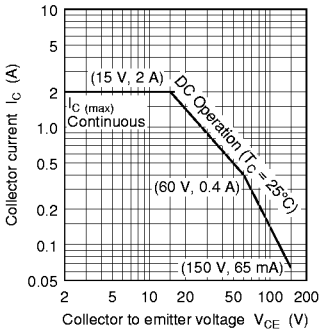
Note: 1. The 2SD1138 is grouped by h_{FE1} as follows.
2. Pulse test.

B	C	D
60 to 120	100 to 200	160 to 320

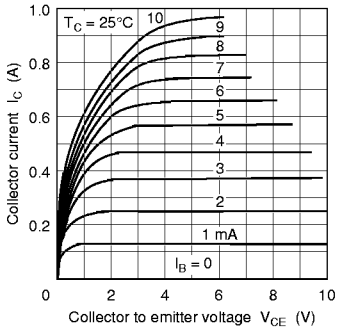
Maximum Collector Dissipation Curve



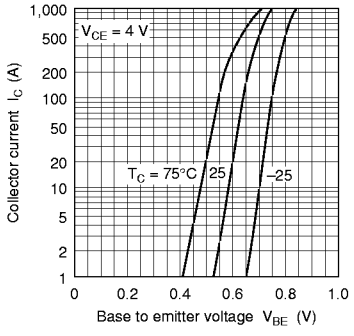
Area of Safe Operation



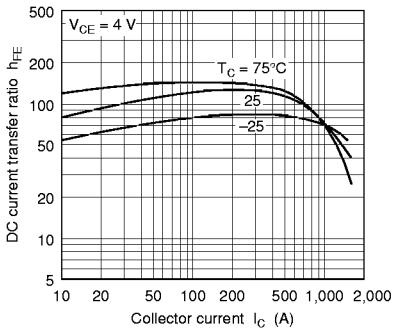
Typical Output Characteristics



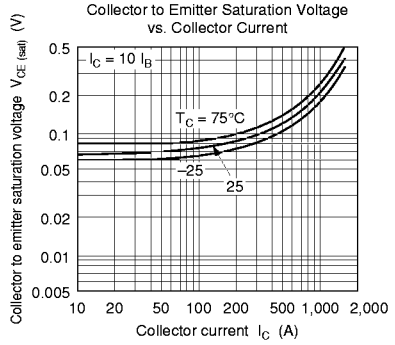
Typical Transfer Characteristics



DC Current Transfer Ratio
vs. Collector Current



Collector to Emitter Saturation Voltage
vs. Collector Current



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